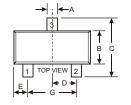


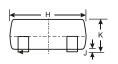
# **MMBD6100**

#### MONOLITHIC DUAL SWITCHING DIODES

#### **Features**

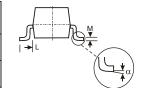
- High conductance.
- Fast switching.
- Surface mount package ideally suited for automatic insertion
- Marking Code:5BM





### Maximum Ratings @ T<sub>A</sub> = 25°C unless otherwise specified

Parameter	Symbol	Limit	Unit
Non-Repetitive Peak Reverse Voltage	V <sub>R</sub>	70	V
Average Rectified Output Current	lo	200	mA
Peak Forward Surge Current @t=1.0μs	I <sub>FSM</sub>	2.0	Α
Power Dissipation	P <sub>D</sub>	350	mW
Thermal Resistance	$R_{\theta JA}$	357	°C/W
Junction Temperature	TJ	150	°C
Storage Temperature Range	T <sub>STG</sub>	-65~+150	°C



Dim	Min	Max			
Α	0.37	0.51			
В	1.20	1.40			
С	2.30	2.50			
D	0.89	1.03			
E	0.45	0.60			
G	1.78	2.05			
Н	2.80	3.00			
J	0.013	0.10			
K	0.903	1.10			
L	0.45	0.61			
М	0.085	0.180			
α	0°	8°			
All Dimensions in mm					

SOT-23

#### **Equivalent Circuit**



## Electrical Characteristics @ T<sub>A</sub> = 25°C unless otherwise specified

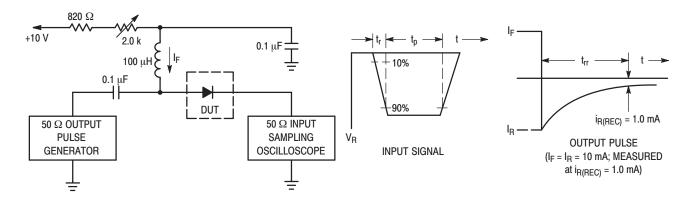
Characteristic	ymbol	Min	MAX	UNIT	Test Condition
Reverse Breakdown Voltage	V <sub>(BR)R</sub>	70		V	I <sub>R</sub> = 100μA
Forward Voltage	V <sub>F</sub>	0.55 0.85	0.7 1.1	V	I <sub>F</sub> =1mA I <sub>F</sub> =100mA
Reverse Leakage Current	I <sub>R</sub>		0.1	μΑ	V <sub>R</sub> =50V
Junction Capacitance	C <sub>j</sub>		2.5	pF	V <sub>R</sub> =0V,f=1MHz
Reverse Recovery Time	t <sub>rr</sub>		4	ns	$I_F = I_R = 10 \text{mA},$ $I_{RR} = 0.1 \text{*} I_R R_L = 100 \Omega$





#### MONOLITHIC DUAL SWITCHING DIODES

#### TYPICAL TRANSIENT CHARACTERISTICS



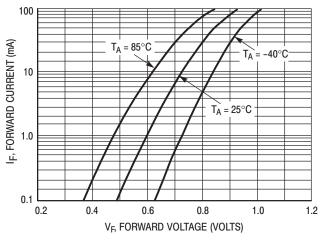
Notes: 1. A 2.0 k $\Omega$  variable resistor adjusted for a Forward Current (I<sub>F</sub>) of 10 mA.

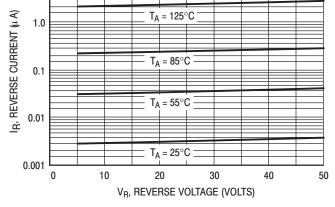
- 2. Input pulse is adjusted so  $I_{R(peak)}$  is equal to 10 mA.
- $3. t_n * t_{rr}$

Figure 1. Recovery Time Equivalent Test Circuit

#### **CURVES APPLICABLE TO EACH CATHODE**

10





 $T_A = 150^{\circ}C$ 

Figure 2. Forward Voltage

Figure 3. Leakage Current

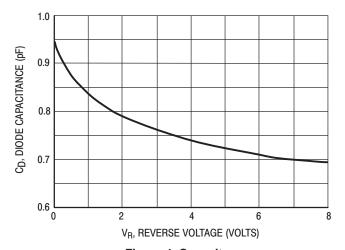


Figure 4. Capacitance

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# **MMBD6100**

#### MONOLITHIC DUAL SWITCHING DIODES

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